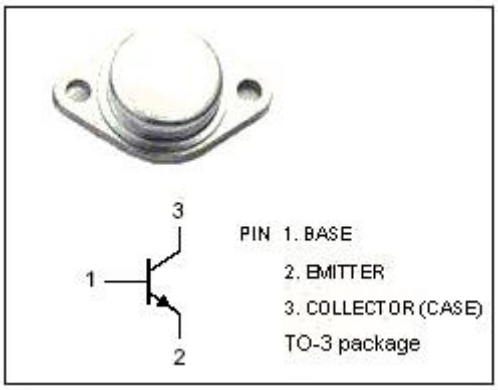
isc Silicon NPN Power Transistor 3DA77

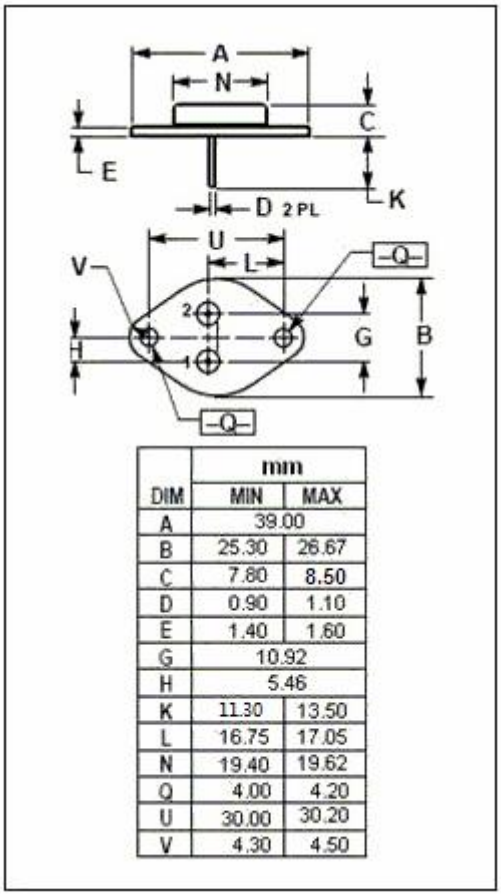


DESCRIPTION

- High DC Current Gain
  : h_{FE}= 10(MAX)@I_C= 1.5A
- Excellent Safe Operating Area
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use as an output device in complementary audio amplifiers



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEO}	Collector-Emitter Voltage	70	V
V_{EBO}	Emitter-Base Voltage	1	V
I_C	Collector Current-Continuous	5.0	A
P_C	Collector Power Dissipation@T_C=75℃	40	W
T_J	Junction Temperature	175	℃
T_{stg}	Storage Temperature Range	-55-175	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.25	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(BR)}$	Collector-Emitter Breakdown Voltage	I_C=20mA; I_B=0	70		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=5A; I_B=1A		3	V
I_{CBO}	Collector Cutoff Current	V_{CB}=24V; I_E=0		3	mA
I_{CEO}	Emitter Cutoff current	V_{CE}=20V; I_C=0		1	mA
h_{FE}	DC Current Gain	I_C=1.5A ; V_{CE}=5V	10		